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**CLAIMS**

7       *What is claimed is:*

8     1.    A method for characterizing an integrated circuit substrate, comprising:  
9              obtaining a substrate doping profile, the substrate doping profile including a  
10          net doping level for each one of a plurality of depths within the integrated circuit  
11          substrate;  
12              vertically discretizing the substrate doping profile to form a vertically  
13          discretized substrate doping profile; and  
14              associating the vertically discretized doping profile with an access key, the  
15          access key comprising a region name and a cross-section name.

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